

High power cycling capability
 Low on-state and switching losses
 Optimized for line frequency rectifiers
 Designed for traction and industrial applications

Rectifier Diode Type D143-1250-18

Average forward current				I_{FAV}	1250 A				
Repetitive peak reverse voltage				V_{RRM}	1000 ÷ 1800 V				
V_{RRM}, V	1000	1100	1200	1300	1400	1500	1600	1800	
Voltage code	10	11	12	13	14	15	16	18	
$T_j, ^\circ C$	-60 ÷ 190								

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{FAV}	Average forward current	A	1250 1500	$T_c=121\text{ }^\circ C$; Double side cooled; $T_c=100\text{ }^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz
I_{FRMS}	RMS forward current	A	1963	$T_c=121\text{ }^\circ C$; Double side cooled; 180° half-sine wave; 50 Hz
I_{FSM}	Surge forward current	kA	22.0 25.0	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$ 180° half-sine wave; 50 Hz ($t_p=10\text{ ms}$); single pulse; $V_R=0\text{ V}$;
			24.0 28.0	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$ 180° half-sine wave; 60 Hz ($t_p=8.3\text{ ms}$); single pulse; $V_R=0\text{ V}$;
I^2t	Safety factor	$A^2s \cdot 10^3$	2420 3125	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$ 180° half-sine wave; 50 Hz ($t_p=10\text{ ms}$); single pulse; $V_R=0\text{ V}$;
			2390 3250	$T_j=T_{j\max}$ $T_j=25\text{ }^\circ C$ 180° half-sine wave; 60 Hz ($t_p=8.3\text{ ms}$); single pulse; $V_R=0\text{ V}$;
BLOCKING				
V_{RRM}	Repetitive peak reverse voltages	V	1000 ÷ 1800	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz;
V_{RSM}	Non-repetitive peak reverse voltages	V	1100 ÷ 1900	$T_{j\min} < T_j < T_{j\max}$; 180° half-sine wave; 50 Hz; single pulse;
V_R	Reverse continuous voltages	V	$0.75 \cdot V_{RRM}$	$T_j = T_{j\max}$;
THERMAL				
T_{stg}	Storage temperature	$^\circ C$	-60 ÷ 50	
T_j	Operating junction temperature	$^\circ C$	-60 ÷ 190	
MECHANICAL				
F	Mounting force	kN	14.0 ÷ 16.0	
a	Acceleration	m/s^2	50	Device unclamped
			100	Device clamped

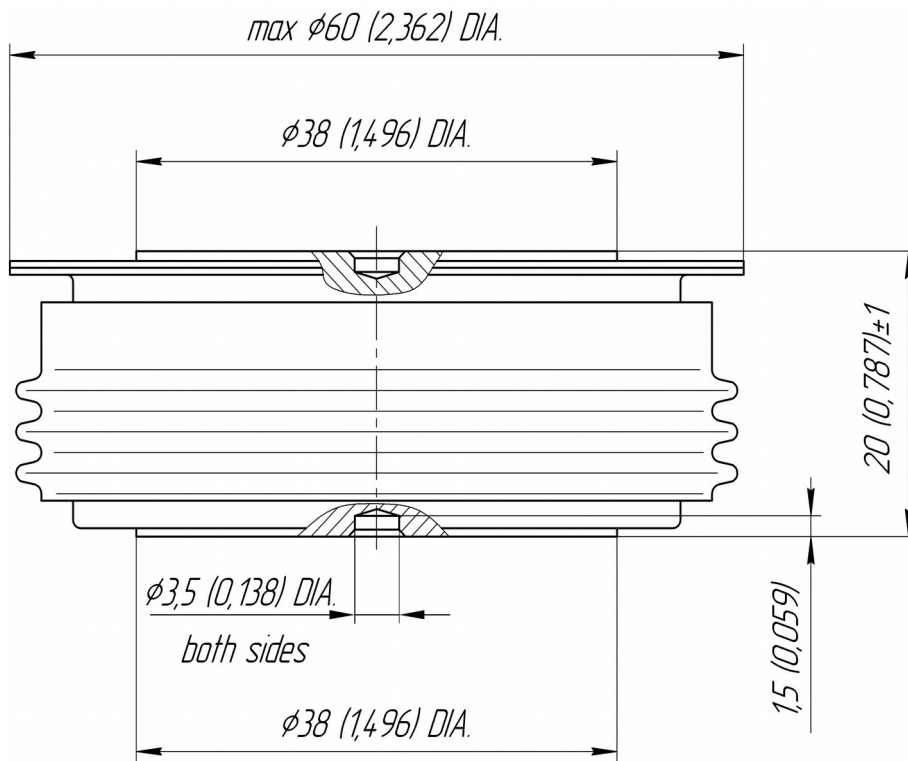
CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{FM}	Peak forward voltage, max	V	1.65	$T_j=25\text{ }^\circ\text{C}; I_{FM}=3925\text{ A}$	
$V_{F(TO)}$	Forward threshold voltage, max	V	0.95	$T_j=T_{j\text{ max}};$	
r_T	Forward slope resistance, max	m Ω	0.250	$0.5\pi I_{FAV} < I_T < 1.5\pi I_{FAV}$	
BLOCKING					
I_{RRM}	Repetitive peak reverse current, max	mA	70	$T_j=T_{j\text{ max}};$ $V_R=V_{RRM}$	
THERMAL					
R_{thjc}	Thermal resistance, junction to case, max	$^\circ\text{C/W}$	0.0320	Direct current	Double side cooled
R_{thjc-A}			0.0704		Anode side cooled
R_{thjc-K}			0.0576		Cathode side cooled
R_{thck}	Thermal resistance, case to heatsink, max	$^\circ\text{C/W}$	0.0060	Direct current	
MECHANICAL					
w	Weight, typ	g	260		
D_s	Surface creepage distance	mm (inch)	23.69 (0.933)		
D_a	Air strike distance	mm (inch)	19.10 (0.752)		

PART NUMBERING GUIDE

D	143	1250	18	N
1	2	3	4	5

1. D — Rectifier Diode
2. Design version
3. Average forward current, A
4. Voltage code
5. Ambient conditions: N – normal; T – tropical



All dimensions in millimeters (inches)

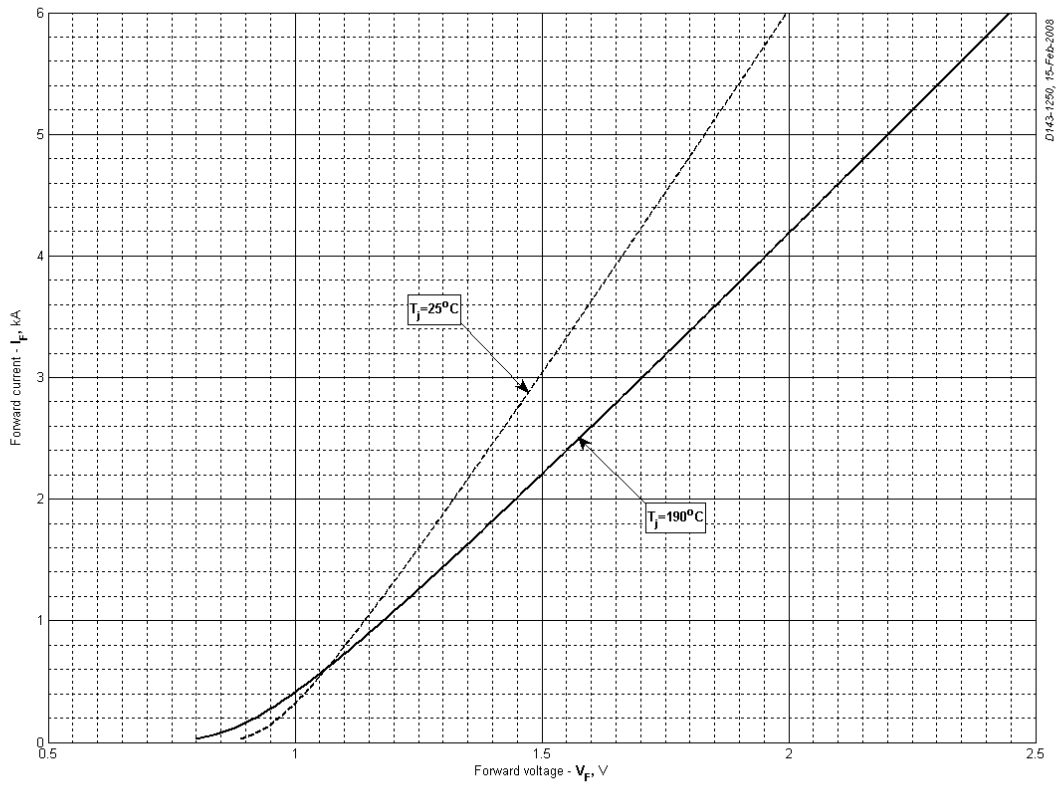


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j \max}$
A	0.843100	0.728162
B	0.131160	0.191782
C	-0.172583	-0.268141
D	0.286381	0.444947

On-state characteristic model (see Fig. 1)

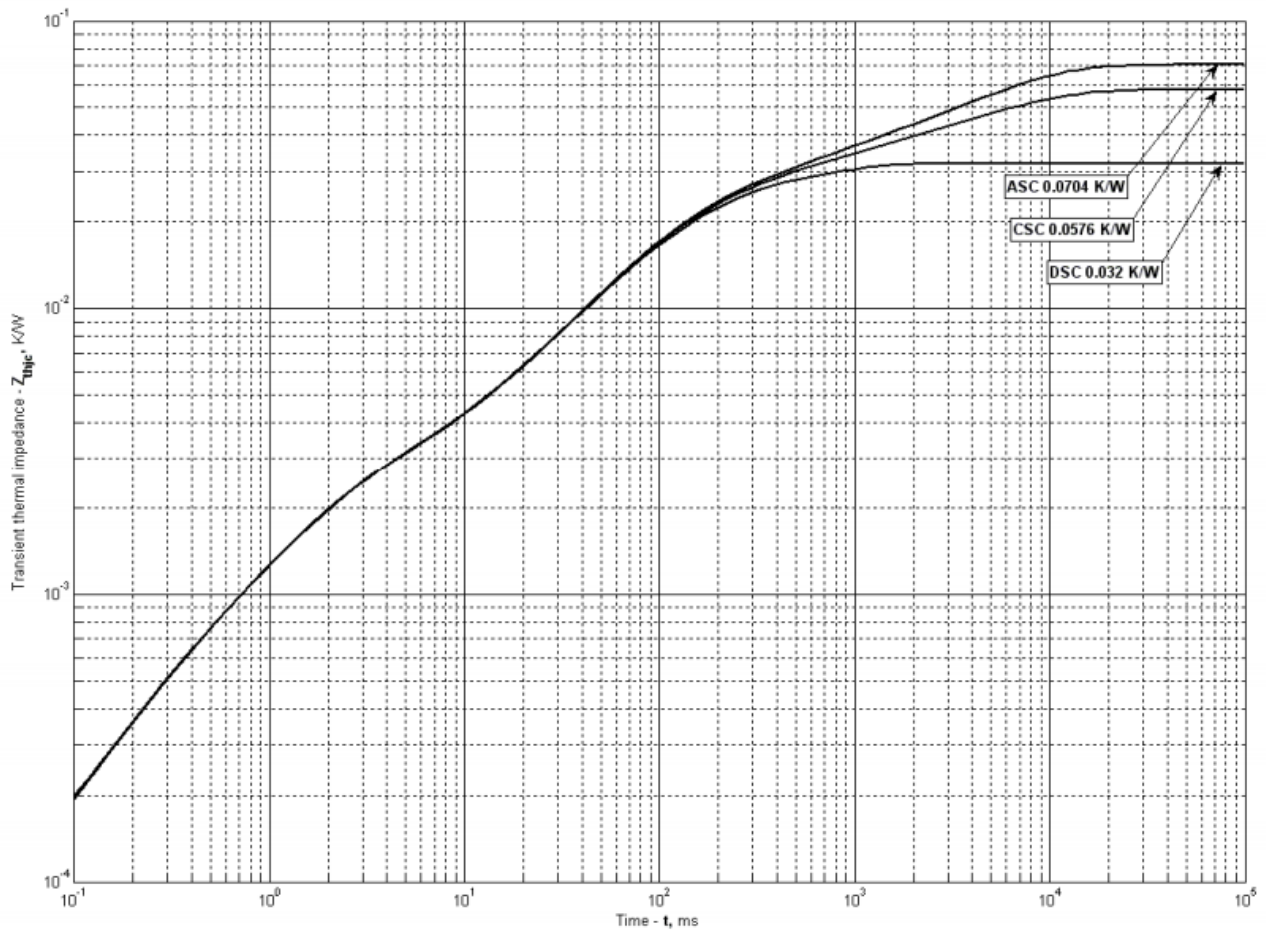


Fig 2 – Transient thermal impedance

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

DC Double side cooled

i	1	2	3	4	5	6
R_i , K/W	0.000005619	0.01031	0.01922	0.0004148	0.001895	0.0001521
τ_i , s	7.790	0.5094	0.09719	0.01725	0.0016	0.0002257

DC Anode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.0381	0.008681	0.01867	0.001961	0.0001787	0.002771
τ_i , s	5.351	0.4584	0.09325	0.001734	0.0002174	0.9059

DC Cathode side cooled

i	1	2	3	4	5	6
R_i , K/W	0.02561	0.0007698	0.01797	0.001931	0.000209	0.01416
τ_i , s	5.328	0.1832	0.09031	0.001714	0.0002598	0.525

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

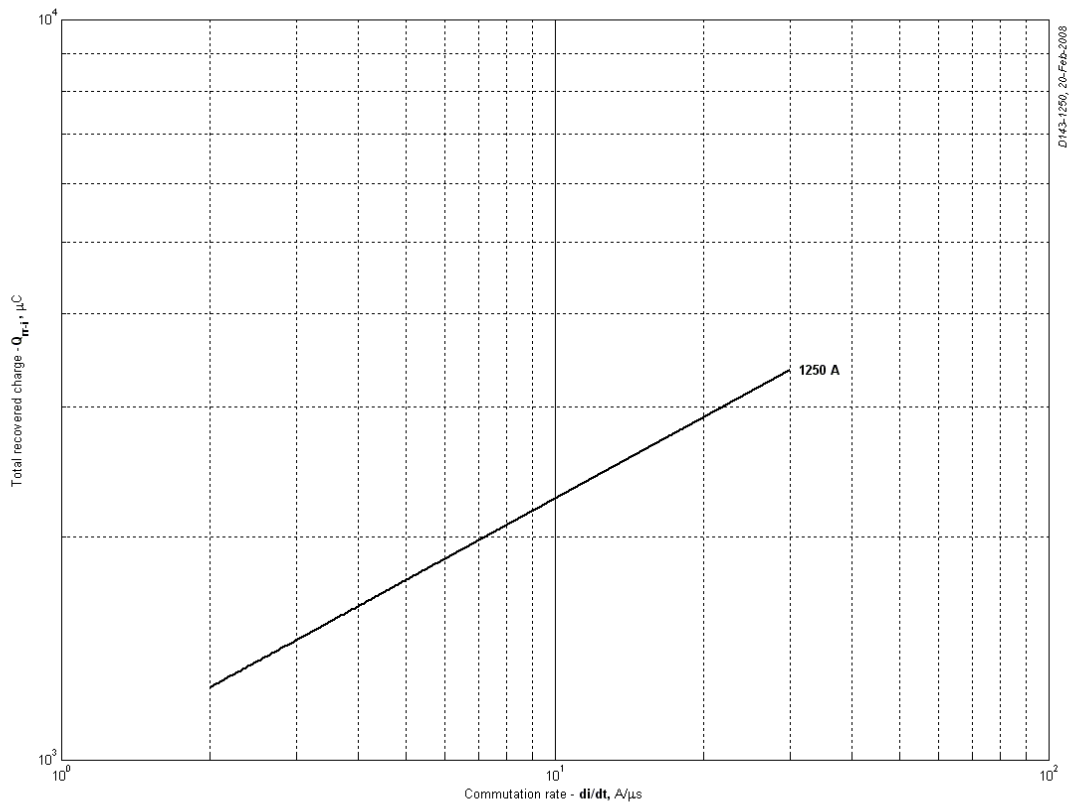


Fig 3 – Total recovered charge, Q_{rr-i} (integral)

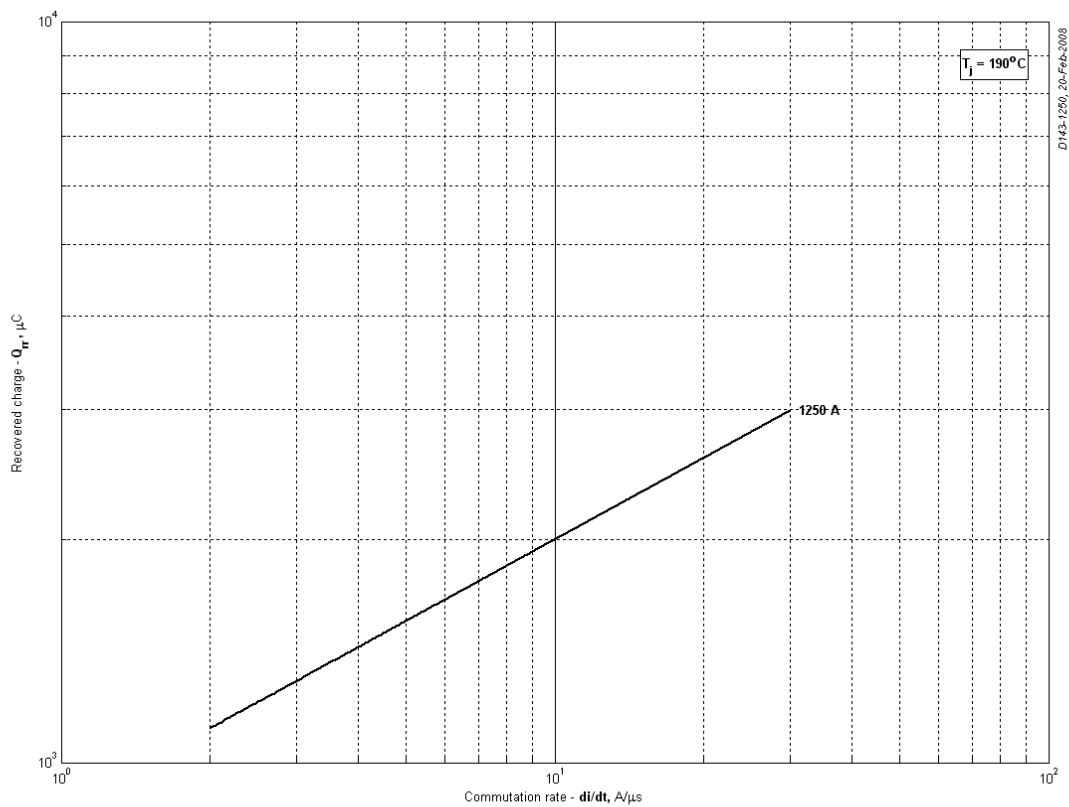


Fig 4 - Recovered charge, Q_{rr} (linear)

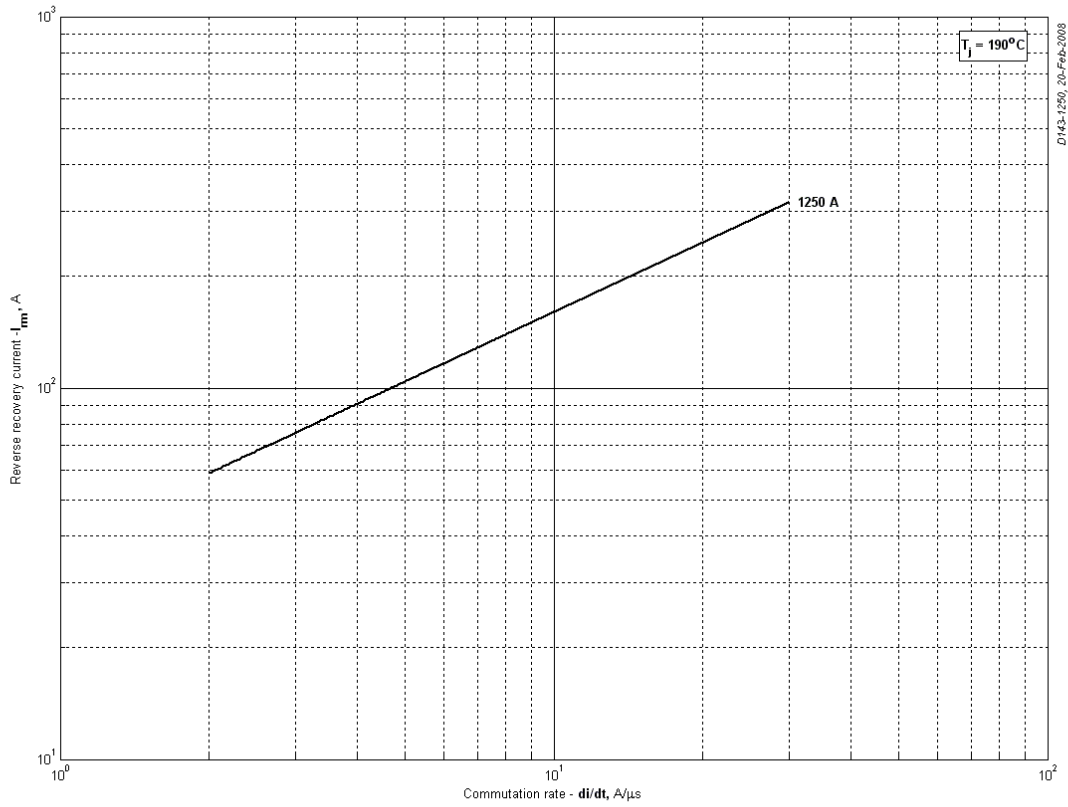


Fig 5 – Peak reverse recovery current, I_{rm}

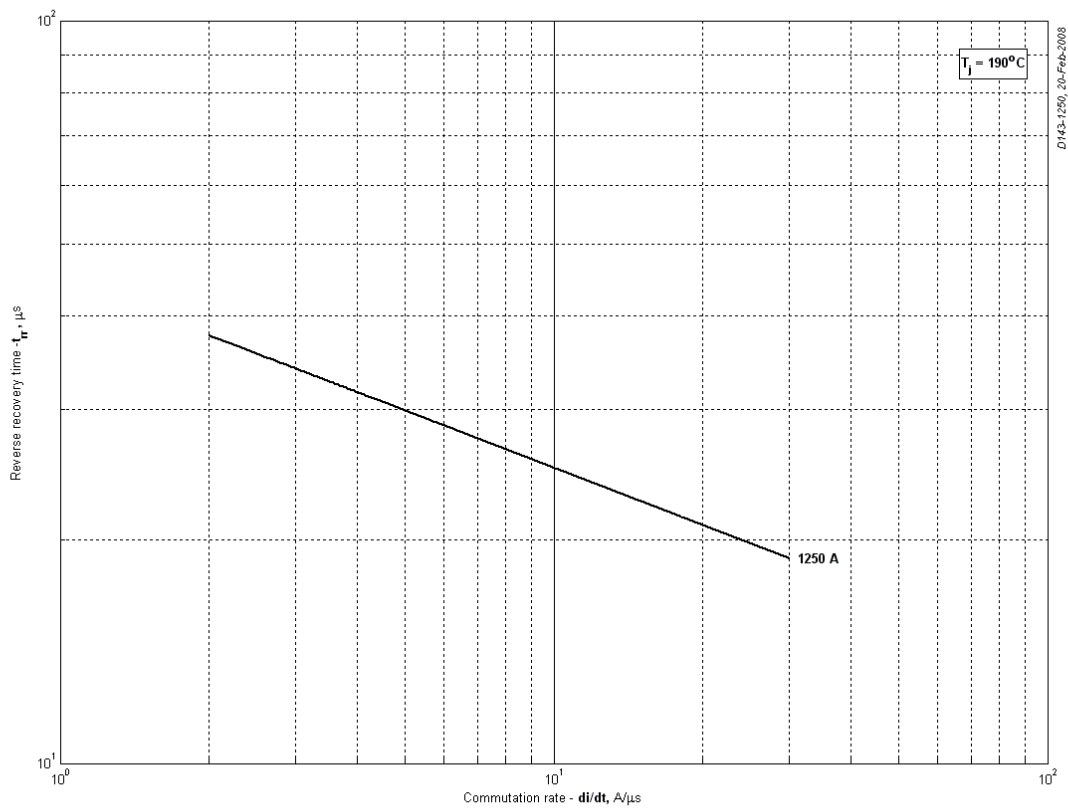


Fig 6 – Maximum recovery time, t_{rr} (linear)

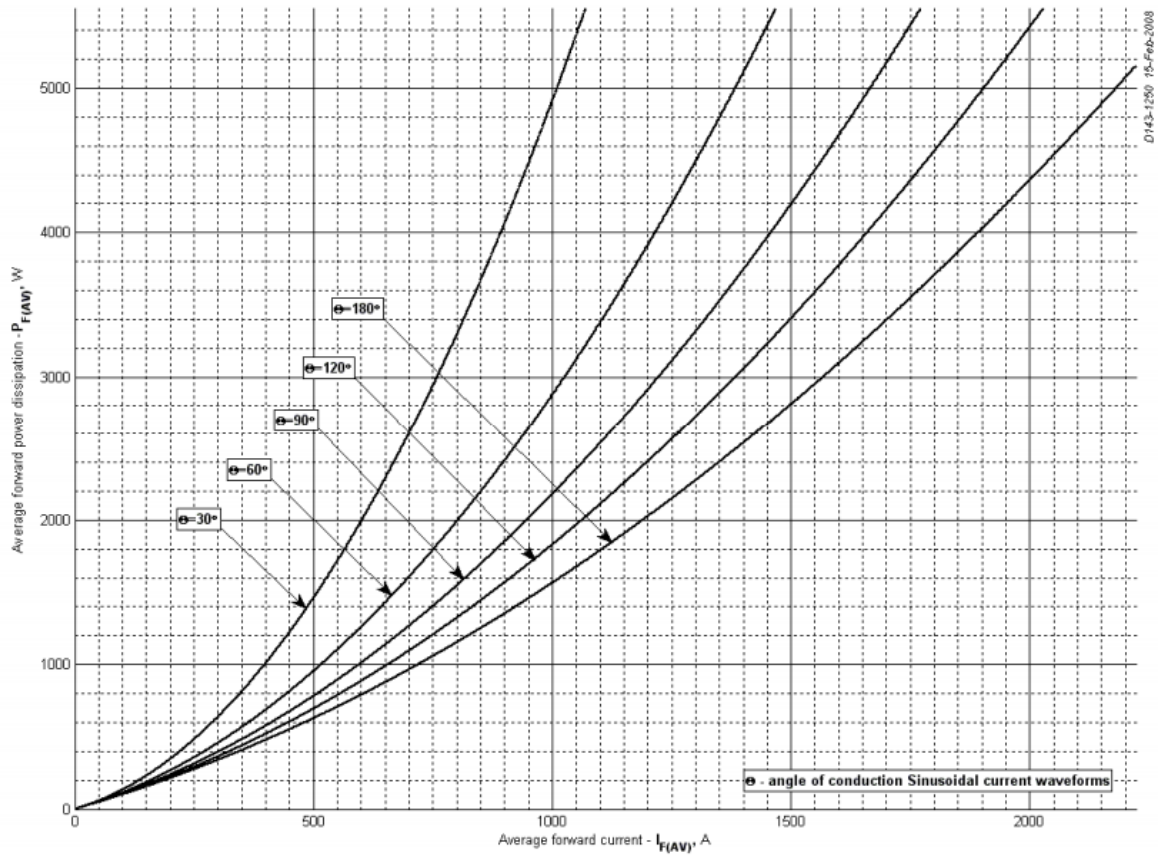


Fig 7 – On-state power loss (sinusoidal current waveforms)

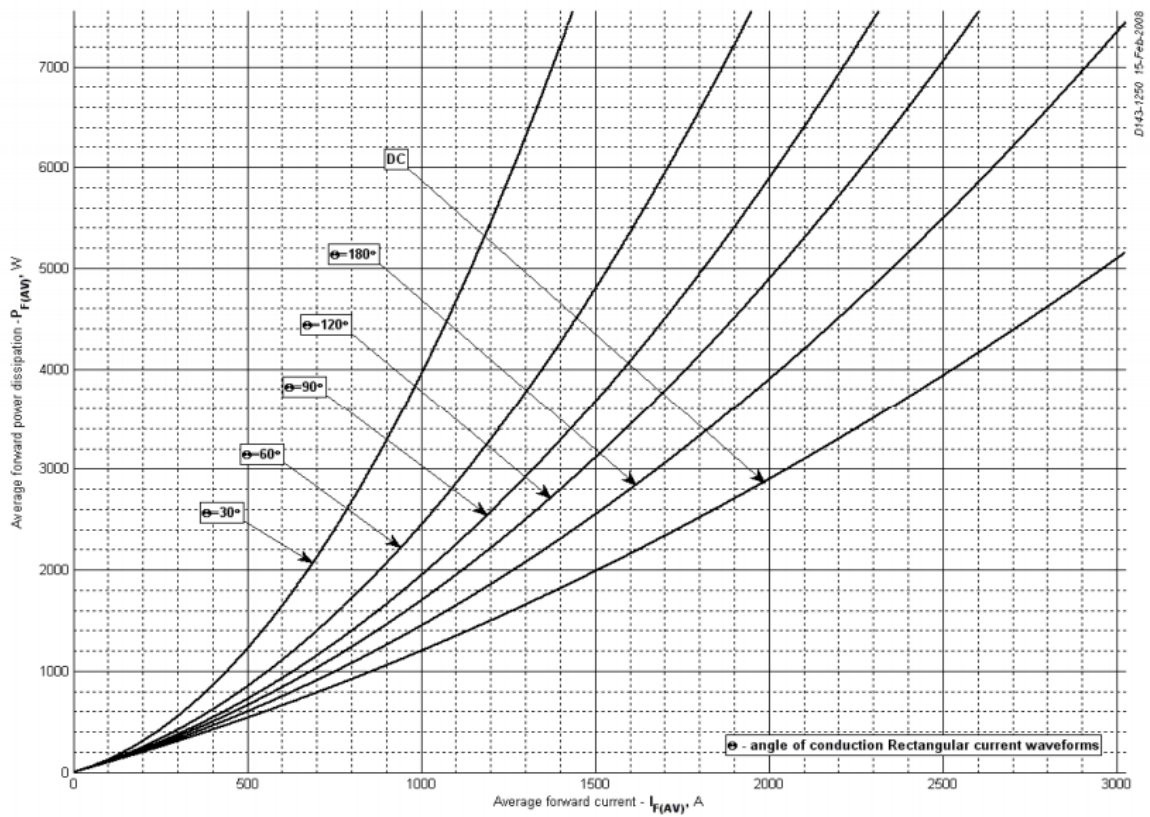
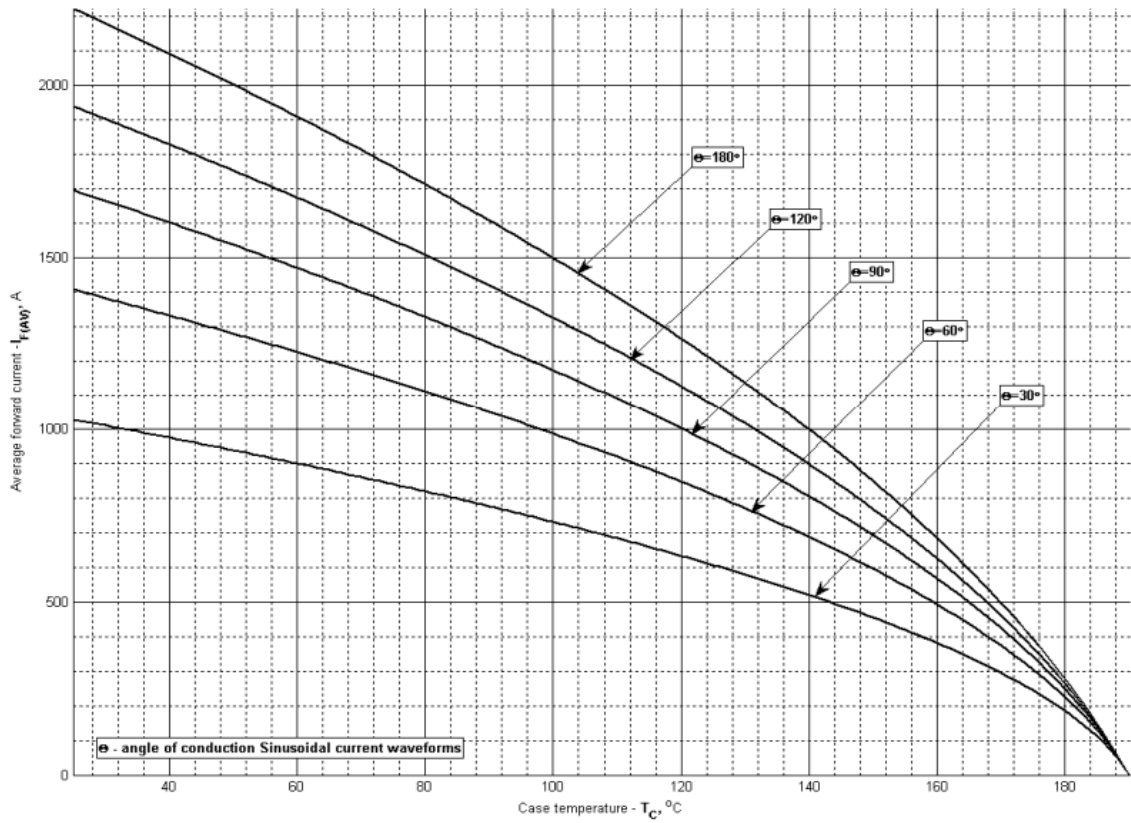
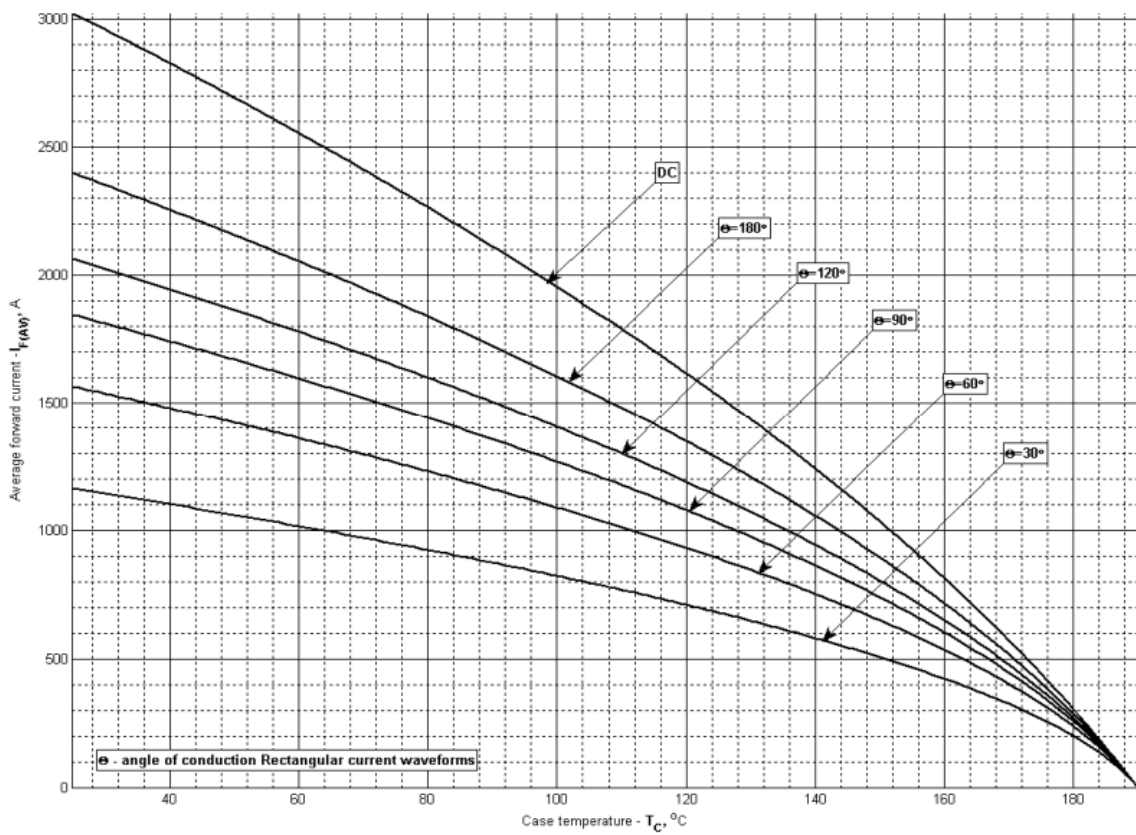


Fig 8 – On-state power loss (rectangular current waveforms)



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Fig 9 – Maximum case temperature DSC (sinusoidal current waveforms)



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Fig 10 – Maximum case temperature DSC (rectangular current waveforms)

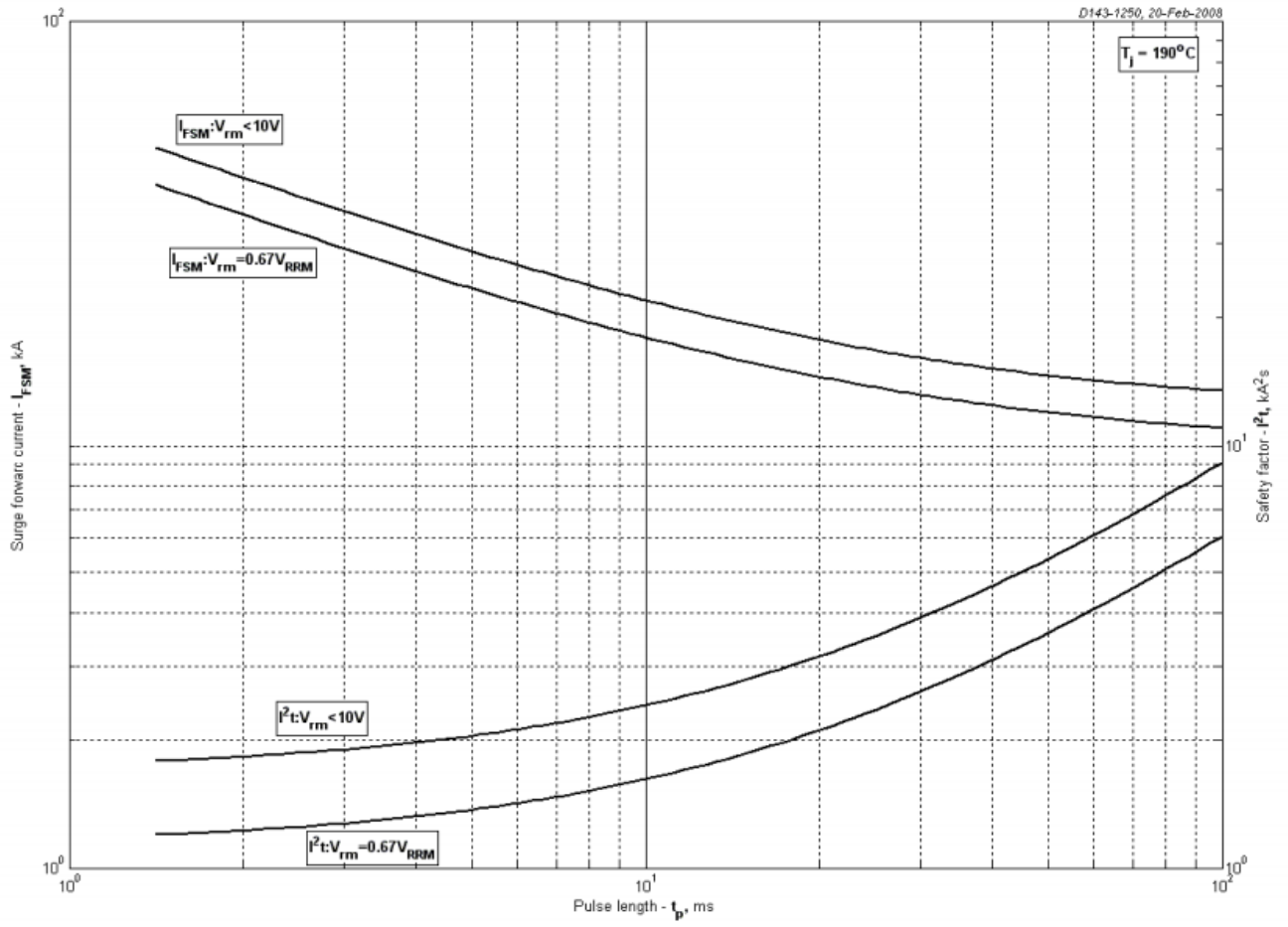


Fig 11 – Maximum surge and I^2t ratings

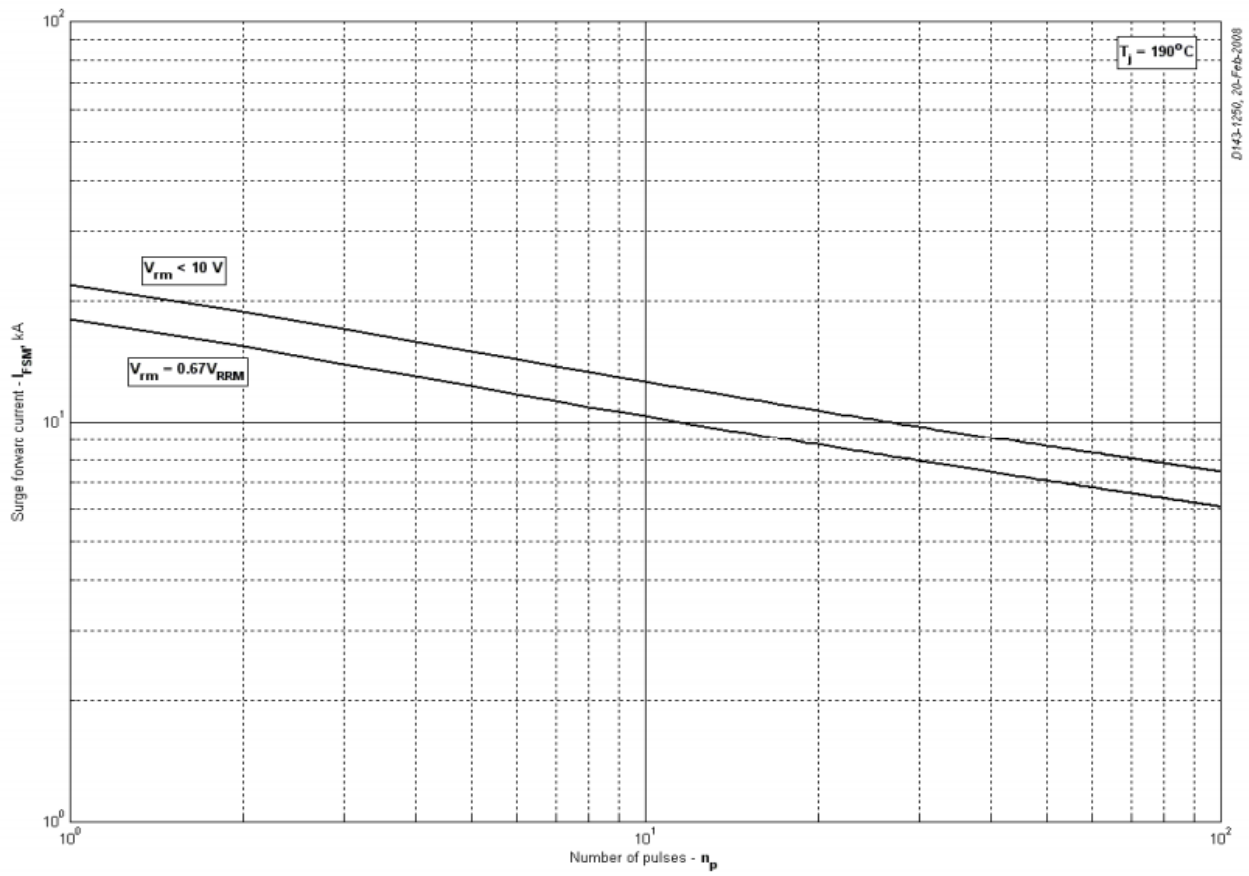


Fig 12 – Maximum surge ratings